

N-Channel Enhancement Mode Power MOSFET

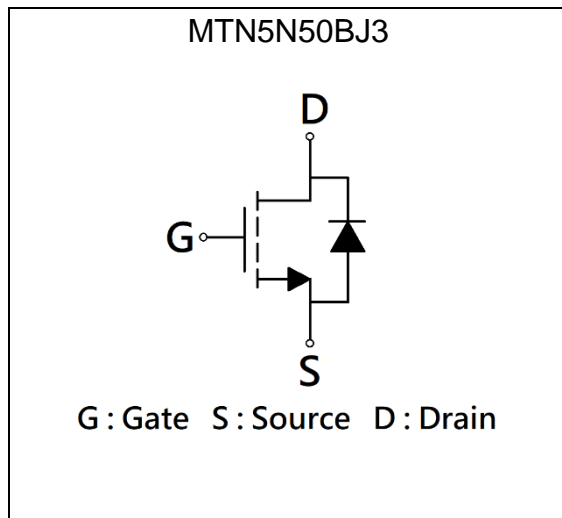
MTN5N50BJ3

Features

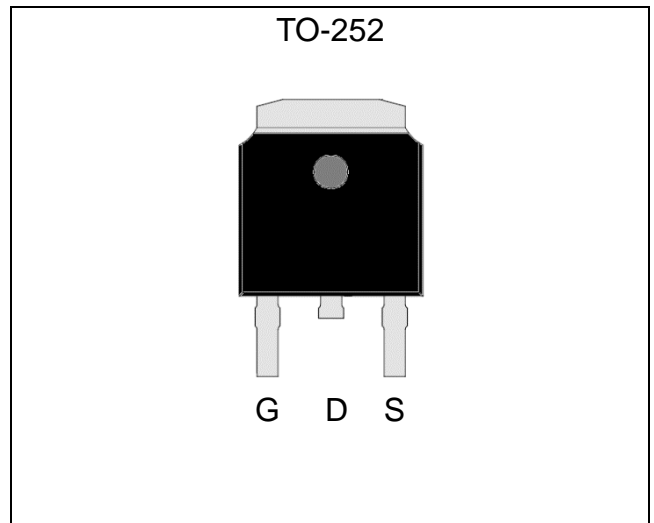
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package
- Pb-free lead plating and halogen-free package

BV_{DSS}	500V
$I_D @ V_{GS}=10V, T_C=25^\circ C$	4.5A
$R_{DS(on)(TYP)} @ V_{GS}=10V, I_D=2.25A$	1.1 Ω

Symbol

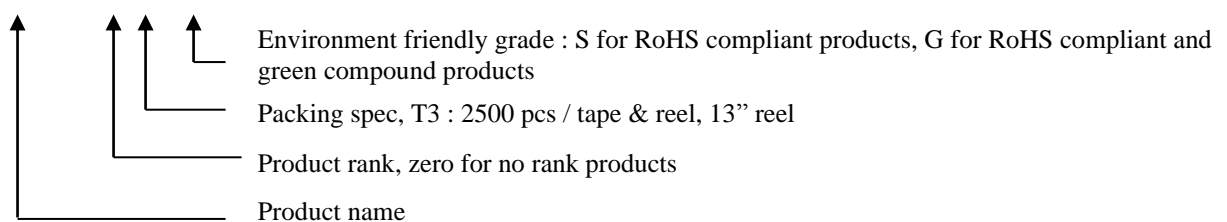


Outline



Ordering Information

Device	Package	Shipping
MTN5N50BJ3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel





Absolute Maximum Ratings (Tc=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	500	V
Gate-Source Voltage	V _{GS}	±30	
Continuous Drain Current @Tc=25°C, VGS=10V	I _D	4.5	A
Continuous Drain Current @Tc=100°C, VGS=10V		2.8	
Pulsed Drain Current (Note 1)	I _{DM}	18	
Single Pulse Avalanche Energy (Note 2)	E _{AS}	90	mJ
Avalanche Current (Note 1)	I _{AS}	4.5	A
Repetitive Avalanche Energy (Note 1)	E _{AR}	4.8	mJ
Maximum Temperature for Soldering @ Lead at 0.125 in(0.318mm) from case for 10 seconds	T _L	300	°C
Total Power Dissipation (T _A =25°C) (Note 4)	P _D	2	W
Total Power Dissipation (Tc=25°C)		48	W
Linear Derating Factor		0.38	W/°C
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{th,j-c}	2.6	°C/W
Thermal Resistance, Junction-to-ambient, max (Note 4)	R _{th,j-a}	50	
Thermal Resistance, Junction-to-ambient, max		110	

Note : 1.Repetitive rating; pulse width limited by maximum junction temperature.

2. I_{AS}=4.5A, V_{DD}=50V, L=8mH, R_G=25Ω, starting T_J=+25°C.

3. I_{SD}≤4.5A, dI/dt≤100A/μs, V_{DD}≤BV_{DSS}, starting T_J=+25°C.

4. When the device is mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C.

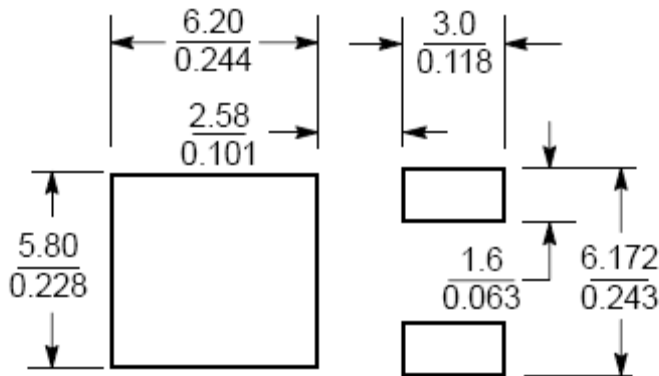
Characteristics (Tc=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	500	-	-	V	V _{GS} =0V, I _D =250μA, T _J =25°C
ΔBV _{DSS} /ΔT _J	-	0.6	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	5	-	S	V _{DS} =15V, I _D =2.25A
I _{GSS}	-	-	±100	nA	V _{GS} =±30V
I _{DSS}	-	-	1	μA	V _{DS} =500V, V _{GS} =0V
	-	-	10		V _{DS} =400V, V _{GS} =0V, T _C =125°C
*R _{DS(ON)}	-	1.1	1.5	Ω	V _{GS} =10V, I _D =2.25A
Dynamic					
*Q _g	-	17.4	-	nC	V _{DD} =400V, I _D =4.5A, V _{GS} =10V
*Q _{gs}	-	3.4	-		
*Q _{gd}	-	7.6	-		

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
*t _{d(ON)}	-	10.6	-	ns	V _{DD} =250V, I _D =4.5A, V _{GS} =10V, R _G =25Ω
*t _r	-	10	-		
*t _{d(OFF)}	-	35	-		
*t _f	-	31.2	-		
C _{iss}	-	572	-	pF	V _{DS} =25V, V _{GS} =0V, f=1MHz
C _{oss}	-	65	-		
C _{rss}	-	32	-		
Source-Drain Diode					
*I _S	-	-	4.5	A	
*I _{SM}	-	-	18		
*V _{SD}	-	-	1.5	V	I _S =4.5A, V _{GS} =0V
*t _{rr}	-	260	-	ns	V _{GS} =0, I _F =4.5A, dI _F /dt=100A/μs
*Q _{rr}	-	1.1	-	μC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

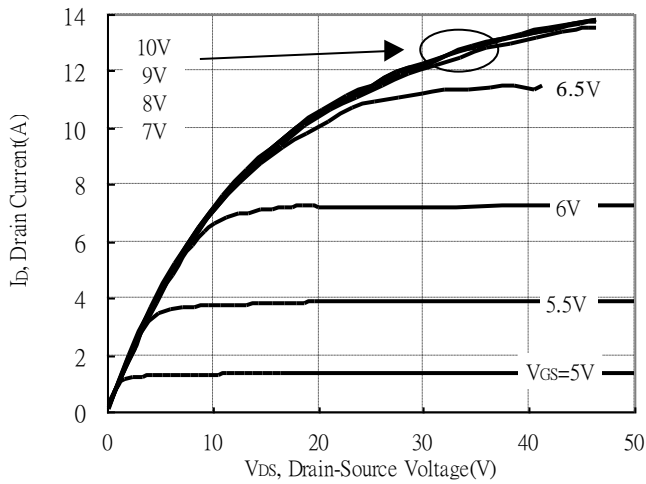
Recommended soldering footprint



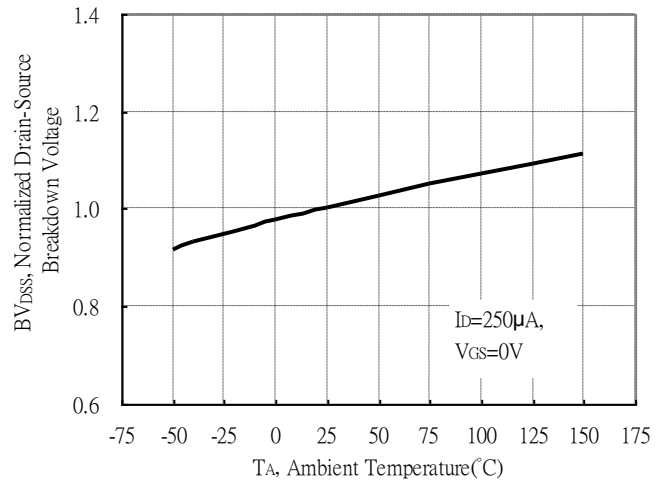
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

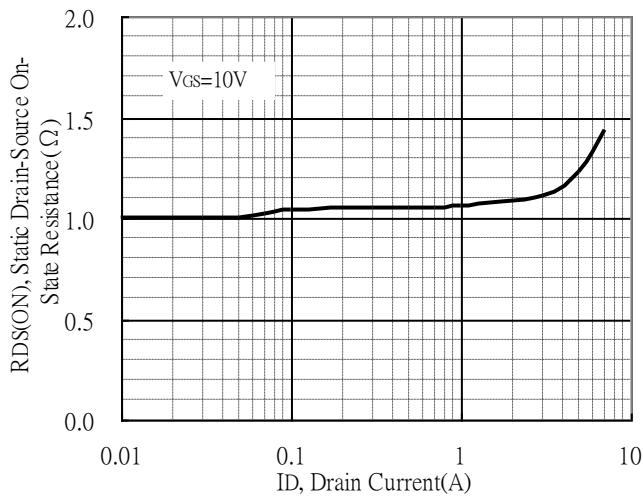
Typical Output Characteristics



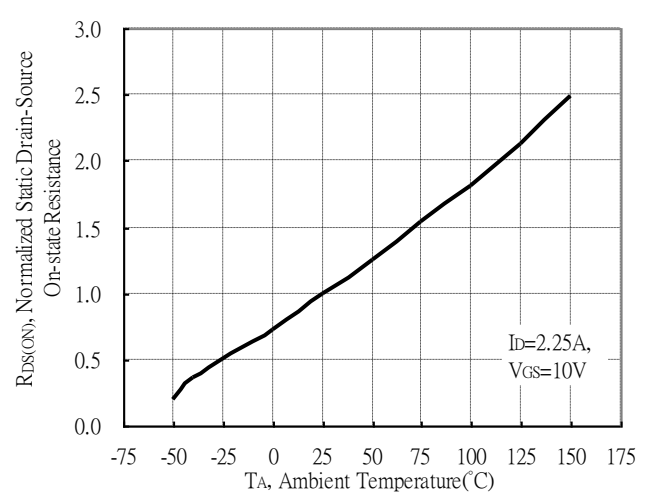
Brekdown Voltage vs Ambient Temperature



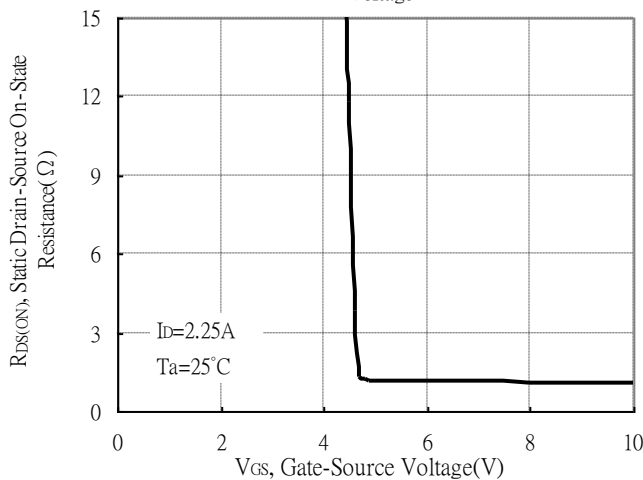
Static Drain-Source On-State resistance vs Drain Current



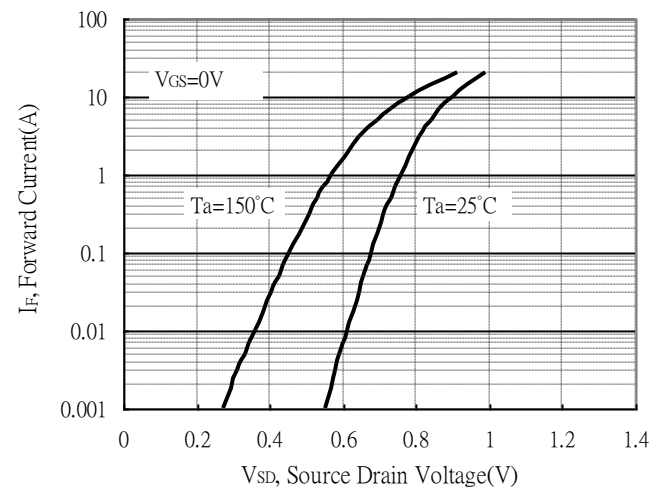
Static Drain-Source On-resistance vs Ambient Temperature



Static Drain-Source On-State Resistance vs Gate-Source Voltage

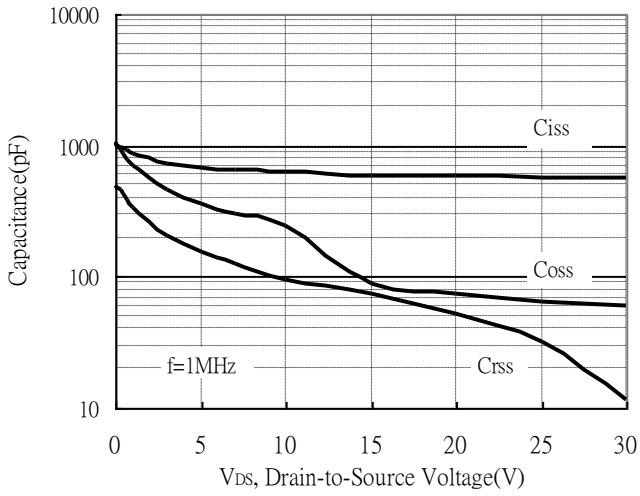


Forward Drain Current vs Source-Drain Voltage

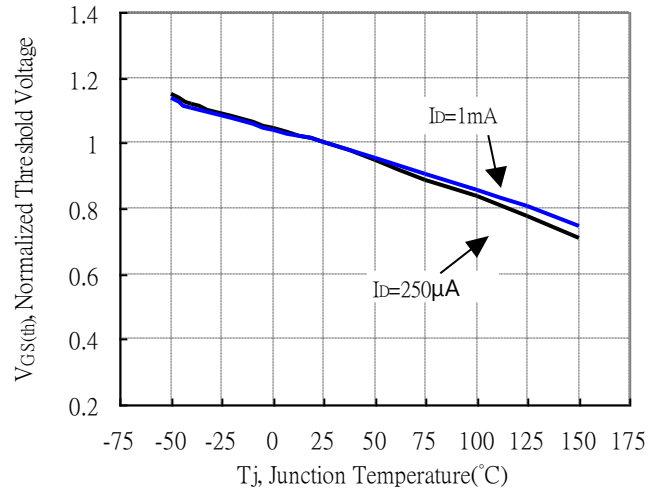


Typical Characteristics(Cont.)

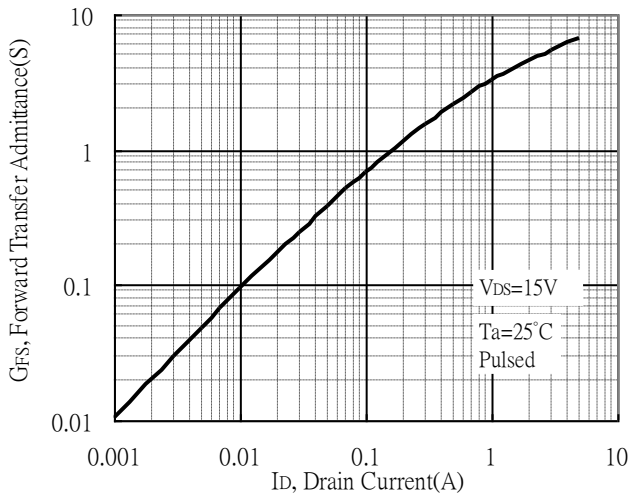
Capacitance vs Reverse Voltage



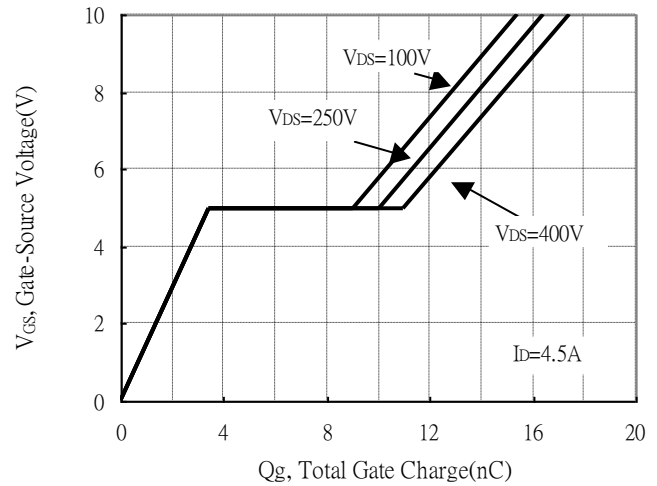
Threshold Voltage vs Junction Temperature



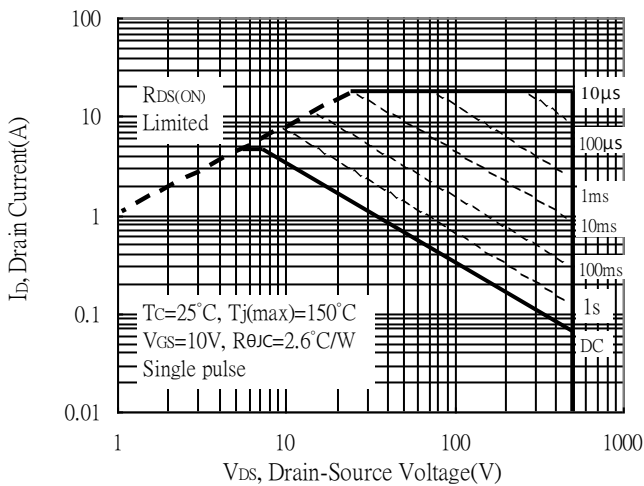
Forward Transfer Admittance vs Drain Current



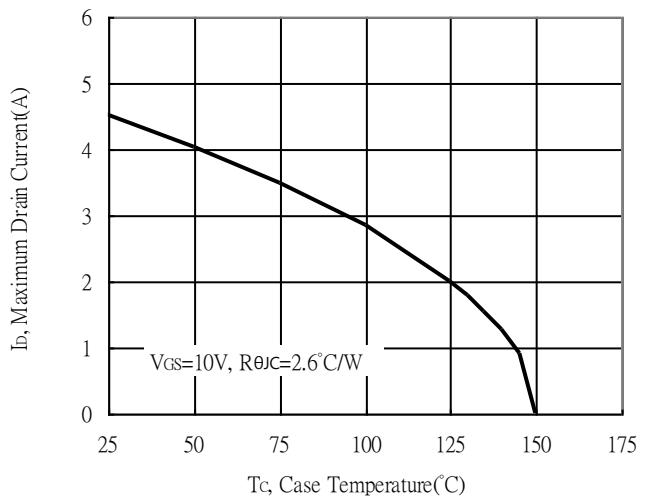
Gate Charge Characteristics



Maximum Safe Operating Area

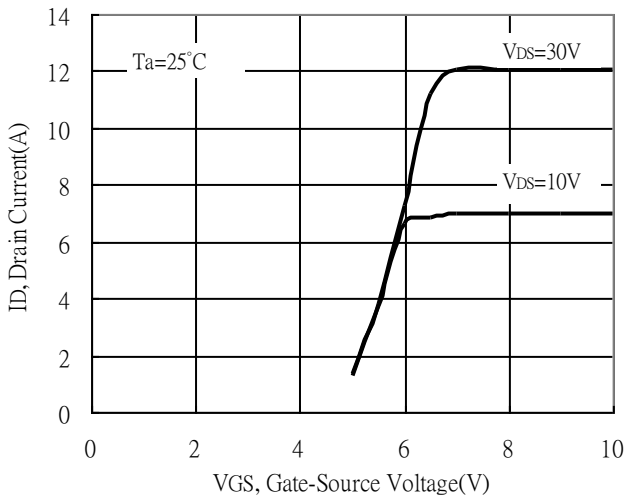


Maximum Drain Current vs Case Temperature

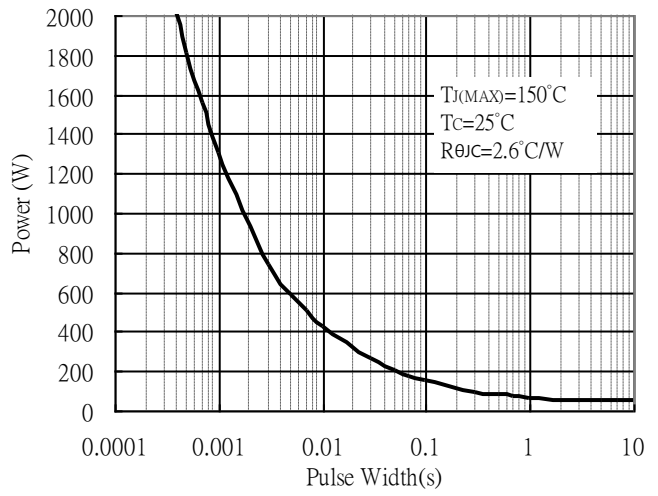


Typical Characteristics(Cont.)

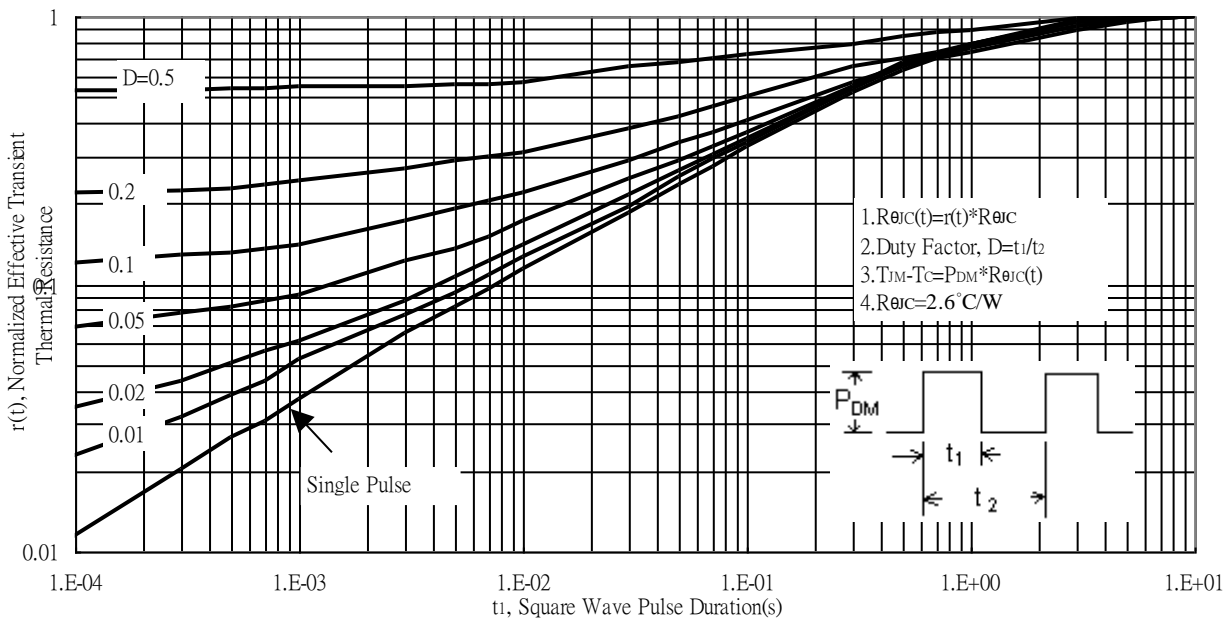
Drain Current vs Gate-Source Voltage



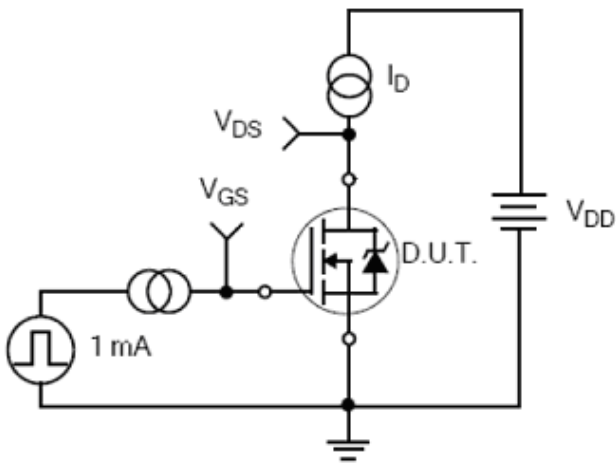
Single Pulse Power Rating, Junction to Case



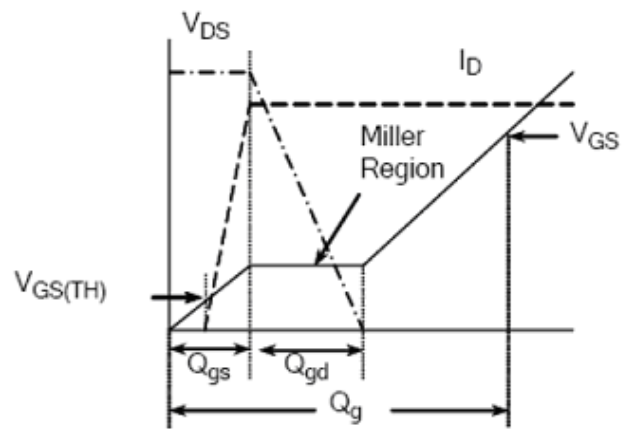
Transient Thermal Response Curves



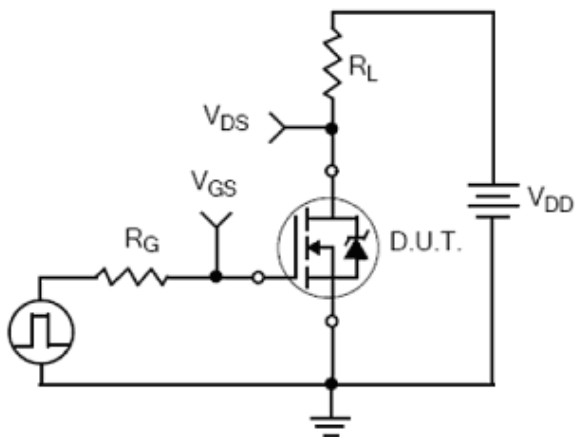
Test Circuit and Waveforms



Gate Charge Test Circuit



Gate Charge Waveform

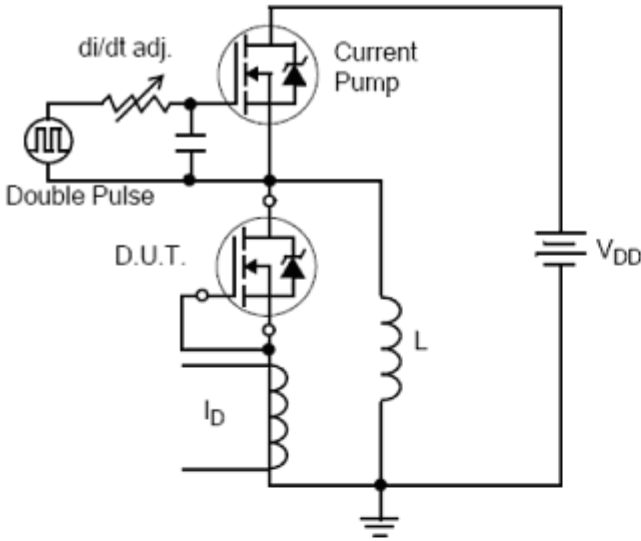


Resistive Switching Test Circuit

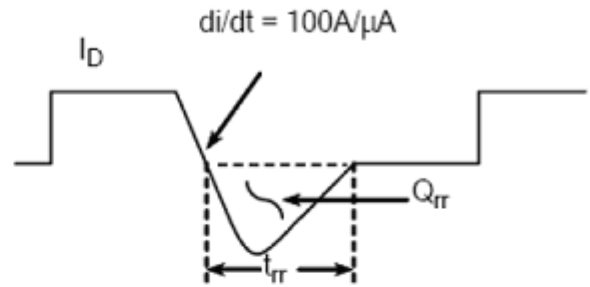


Resistive Switching Waveforms

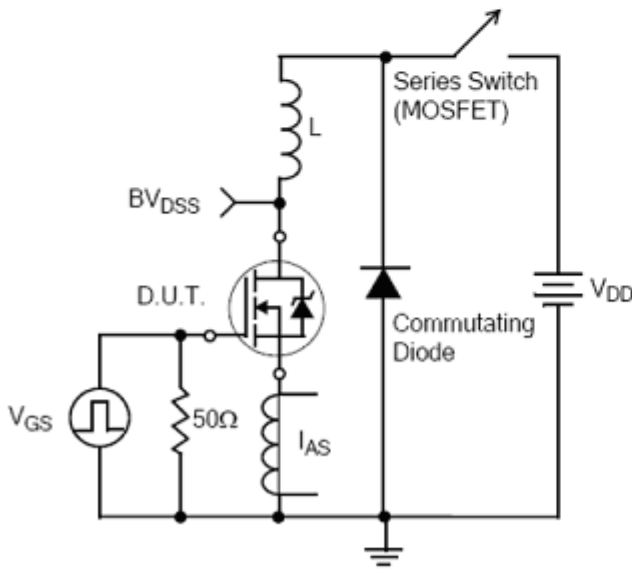
Test Circuit and Waveforms(Cont.)



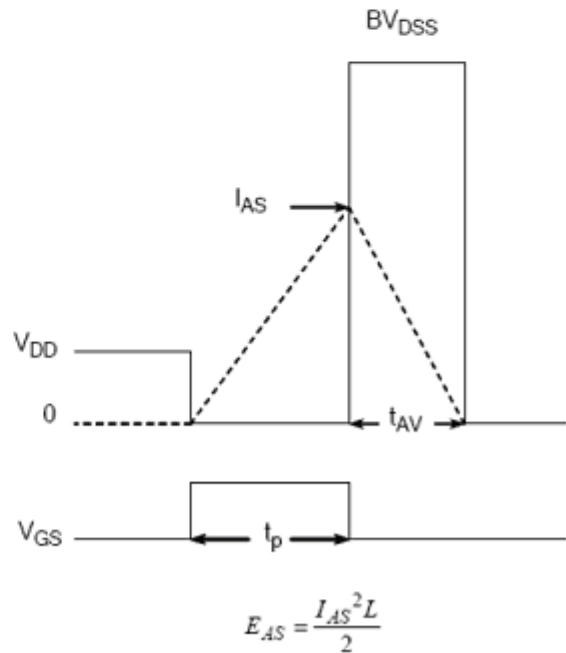
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform

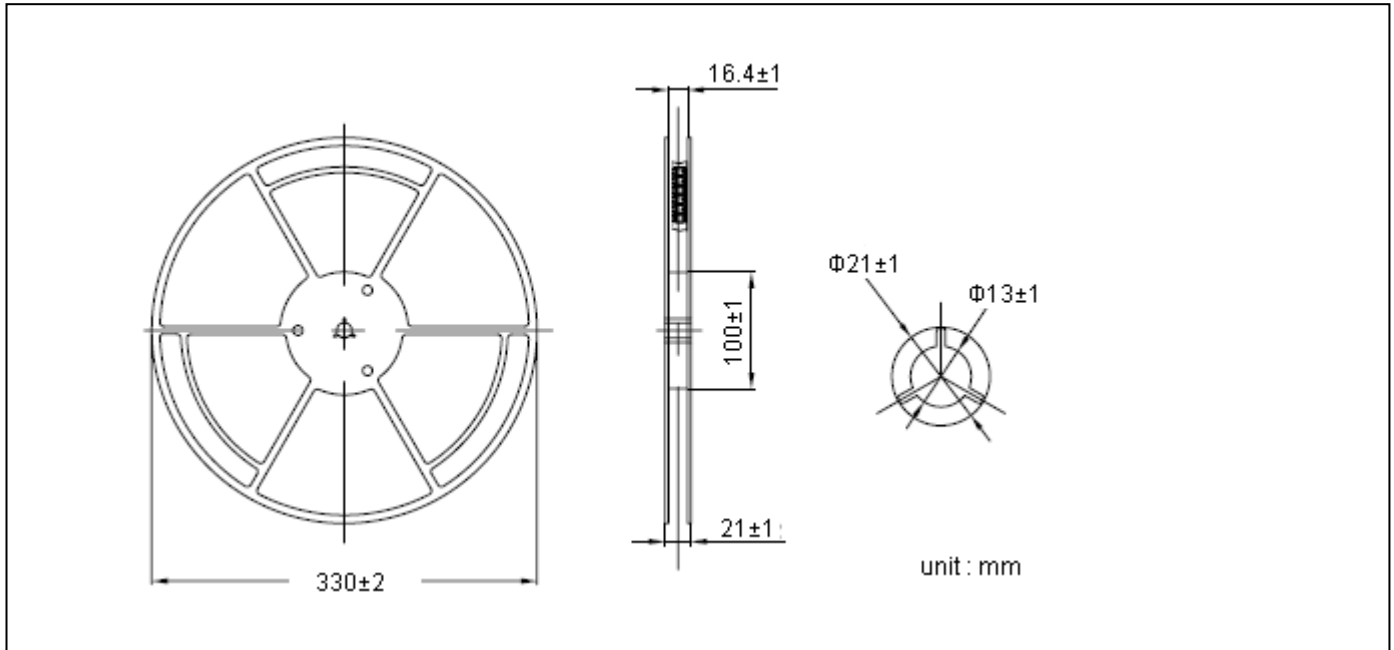


Unclamped Inductive Switching Test Circuit

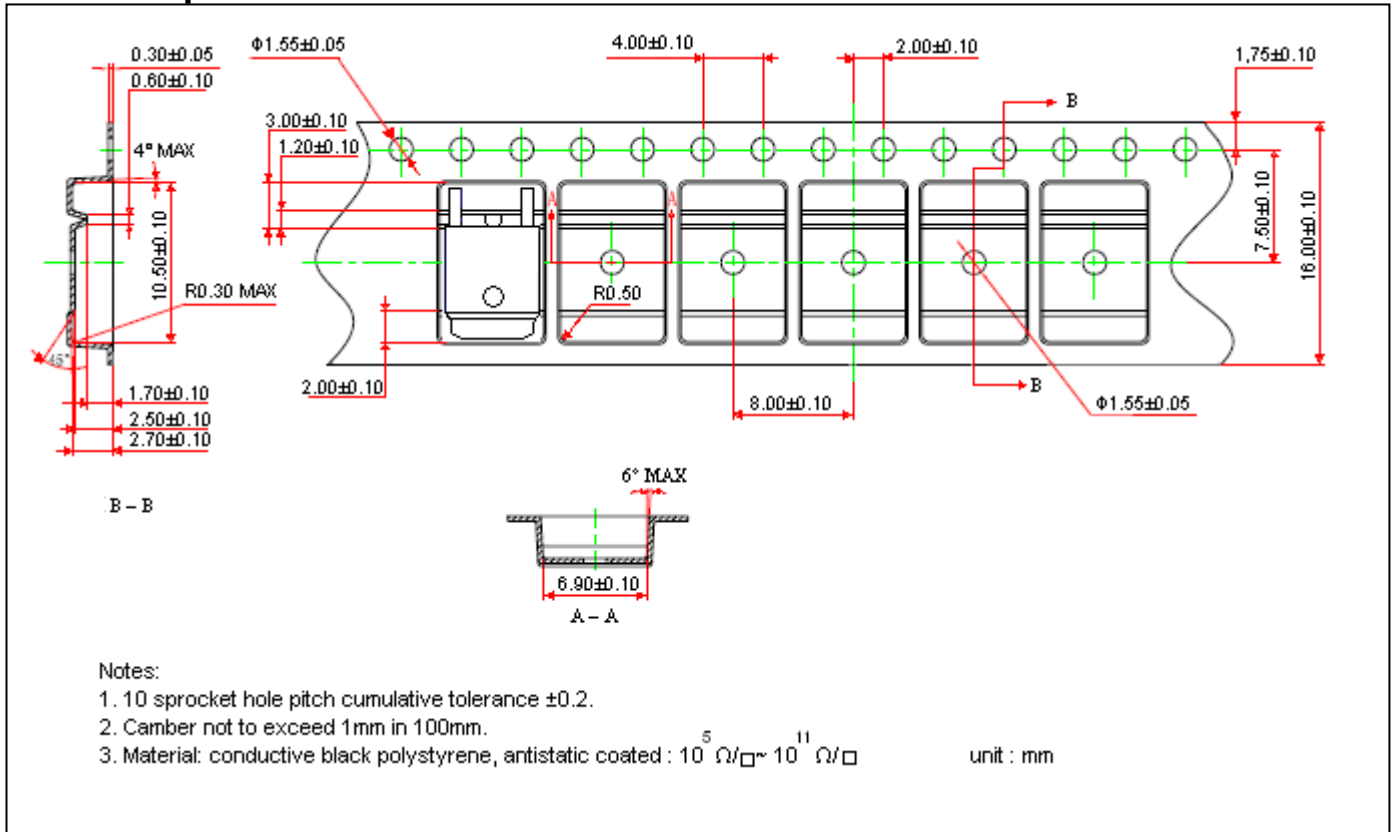


Unclamped Inductive Switching Waveforms

Reel Dimension



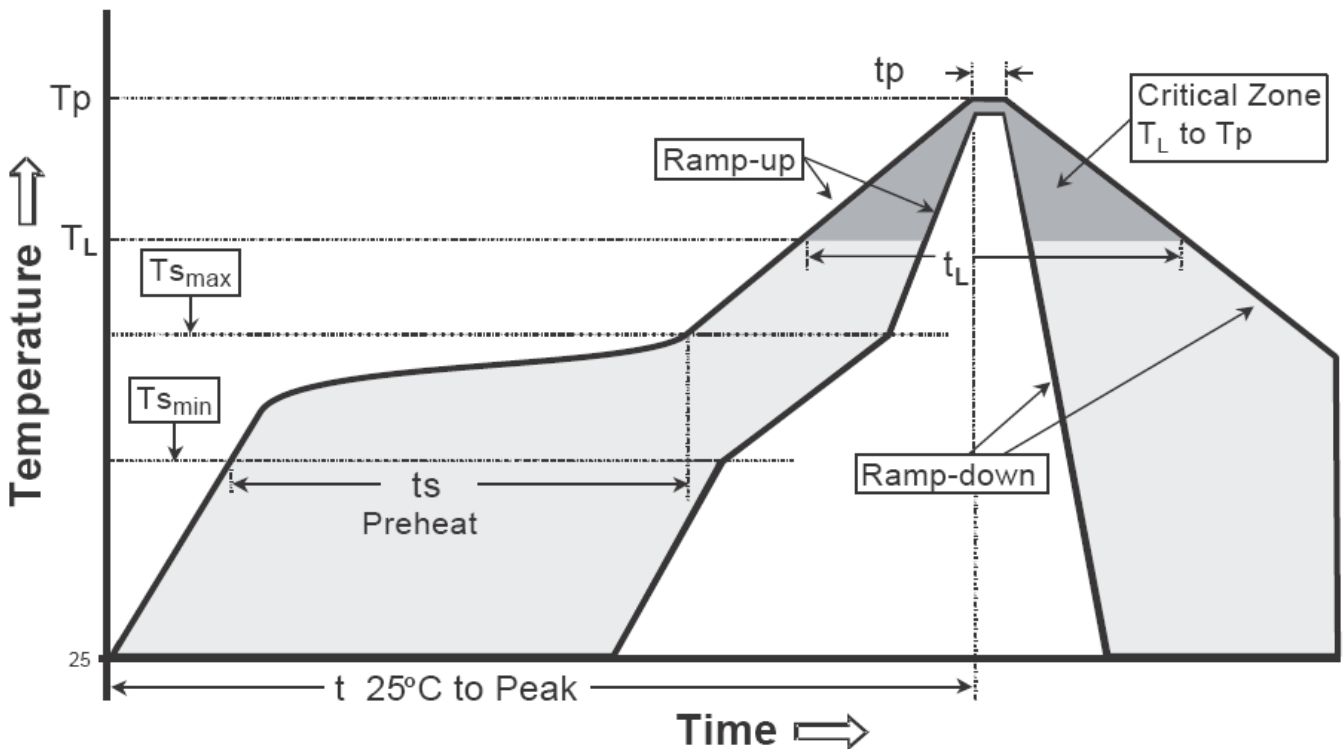
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

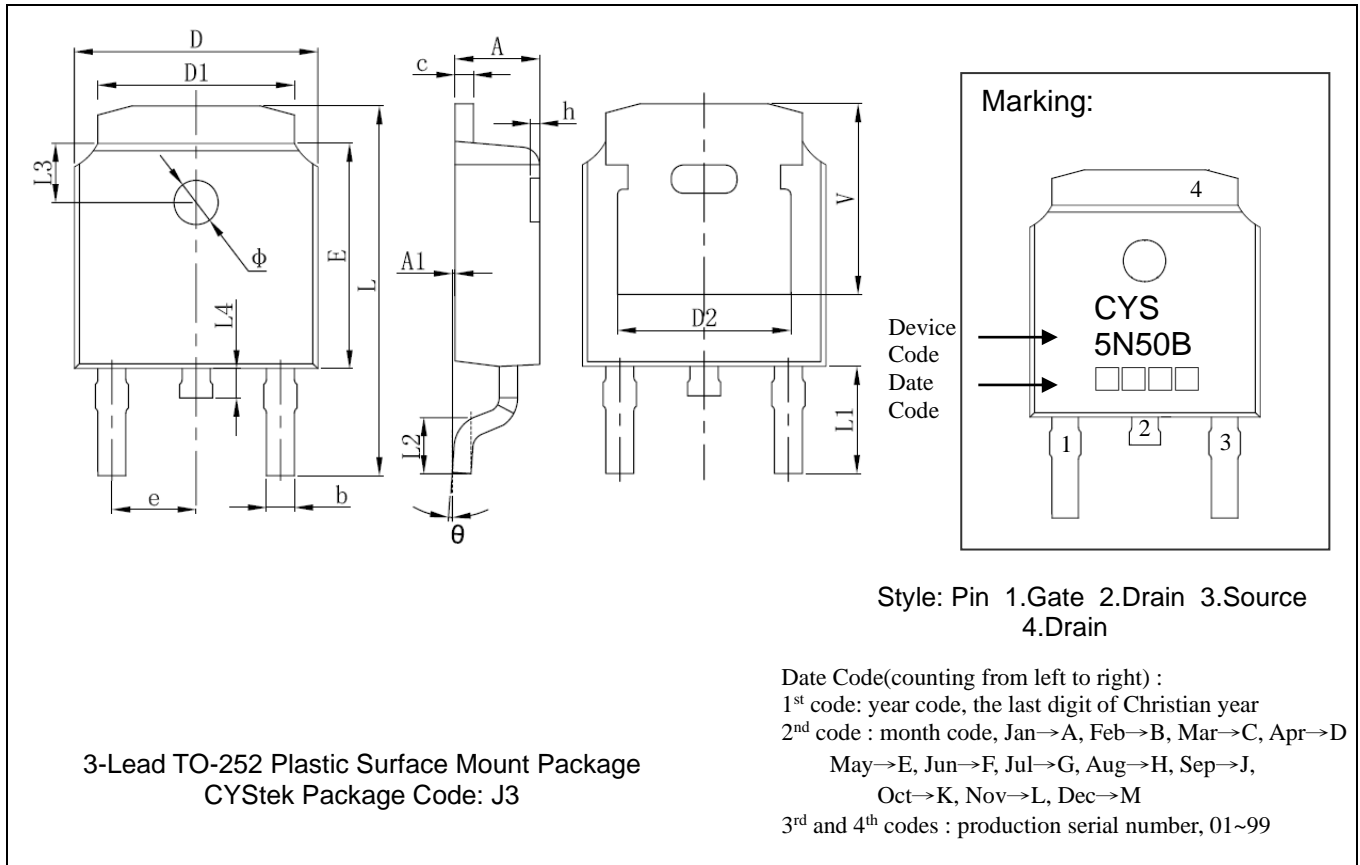
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



3-Lead TO-252 Plastic Surface Mount Package
 CYStek Package Code: J3

Style: Pin 1.Gate 2.Drain 3.Source
 4.Drain

Date Code(counting from left to right) :
 1st code: year code, the last digit of Christian year
 2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D
 May→E, Jun→F, Jul→G, Aug→H, Sep→J,
 Oct→K, Nov→L, Dec→M
 3rd and 4th codes : production serial number, 01~99

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	L	0.382	0.406	9.712	10.312
A1	0.000	0.005	0.000	0.127	L1	0.114	REF	2.900	REF
b	0.025	0.030	0.635	0.770	L2	0.055	0.067	1.400	1.700
c	0.018	0.023	0.460	0.580	L3	0.063	REF	1.600	REF
D	0.256	0.264	6.500	6.700	L4	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	Φ	0.043	0.051	1.100	1.300
D2	0.190	REF	4.830	REF	θ	0°	8°	0°	8°
E	0.236	0.244	6.000	6.200	h	0.000	0.012	0.000	0.300
e	0.086	0.094	2.186	2.386	V	0.207	REF	5.250	REF

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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